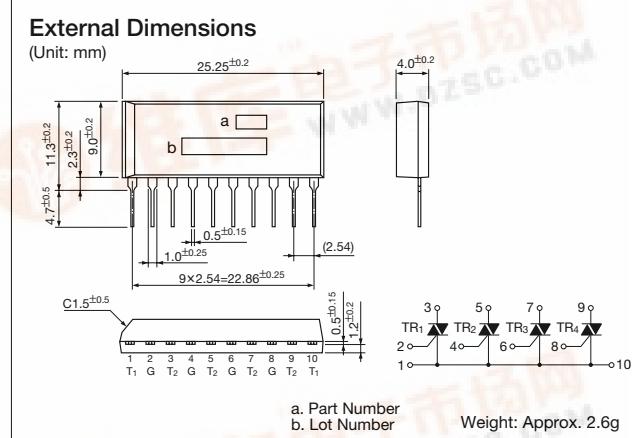


1A 4 circuits Triac Array

STA221A

■ Features

- 1A 4 Triacs combined one package
- Repetitive peak off-state voltage: $V_{DRM}=400V$
- RMS on-state current: $I_{T(RMS)}=1A$
- Gate trigger current: $I_{GT}=3mA$ max (MODE I, II, III)



■ Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit	Conditions
Repetitive peak off-state voltage	V_{DRM}	400	V	-40°C to +125°C
RMS on-state current	$I_{T(RMS)}$	1.0	A	Conduction angle 360°, $T_c=97^\circ C$
Surge on-state current	I_{TSM}	10	A	50Hz full-cycle sinewave, Peak value, Non-repetitive, $T_j=125^\circ C$
Peak forward gate voltage	V_{GM}	6	V	$f \geq 50Hz$, duty $\leq 10\%$
Peak forward gate current	I_{GM}	0.5	A	$f \geq 50Hz$, duty $\leq 10\%$
Peak gate power loss	P_{GM}	1.0	W	$f \geq 50Hz$, duty $\leq 10\%$
Average gate power loss	$P_{G(AV)}$	0.1	W	
Junction temperature	T_j	-40 to +125	°C	
Storage temperature	T_{stg}	-40 to +125	°C	

■ Electrical Characteristics

Parameter	Symbol	Ratings			Unit	Conditions
		min	typ	max		
Off-state current	I_{DRM}		0.1	1.0	mA	$V_D=V_{DRM}$, $R_{GK}=\infty$, $T_j=125^\circ C$
				0.1		$V_D=V_{DRM}$, $R_{GK}=\infty$, $T_j=25^\circ C$
On-state voltage	V_{TM}		1.6		V	$I_{TM}=1.6A$, $T_c=25^\circ C$
Gate trigger voltage	I _G	I	1.7	3.5	V	$V_D=6V$, $R_L=10\Omega$, $T_c=25^\circ C$
		II	0.7	1.2		
		III	0.8	1.2		
		IV	2.0			
Gate trigger current	I _{GT}	I	2.0	3.0	mA	$V_D=6V$, $R_L=10\Omega$, $T_c=25^\circ C$
		II	1.8	3.0		
		III	2.3	3.0		
		IV	13.0			
Gate non-trigger voltage	V_{GD}	0.1			V	$V_D=1/2 \times V_{DRM}$, $T_j=125^\circ C$
Thermal resistance	I _H			20	°C/W	Junction to Lead, 1 element operation
	R _{th}			80		junction to operating environment, 1 element operation